

# **STGW38IH130D**, **STGWT38IH130D**

33 A - 1300 V - very fast IGBT

Datasheet - production data

#### **Features**

- Low saturation voltage
- High current capability
- Low switching loss
- Low static and peak forward voltage drop freewheeling diode

#### **Applications**

- Induction cooking, microwave ovens
- Soft-switching applications

### **Description**

This device is a very fast IGBT developed using advanced PowerMESH™ technology. This process guarantees an excellent trade-off between switching performance and low on-state behavior. This device is well-suited for resonant or soft-switching applications.

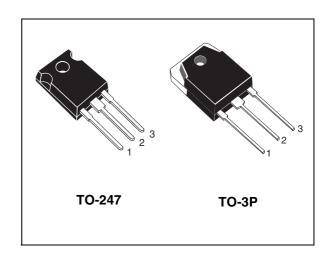


Figure 1. Internal schematic diagram

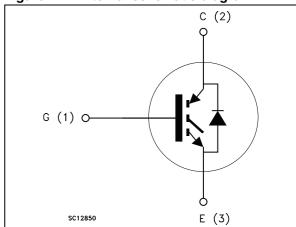


Table 1. Device summary

Order codes	Marking	Package	Packaging
STGW38IH130D		TO-247 long leads	
STGWS38IH130D	GW38IH130D	TO-247	Tube
STGWT38IH130D		TO-3P	

September 2012 Doc ID 15697 Rev 4 1/17

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# 1 Electrical ratings

Table 2. Absolute maximum ratings

		Value	•	
Symbol	Parameter	TO-3P, TO-247 long leads	TO-247	Unit
V <sub>CES</sub>	Collector-emitter voltage (V <sub>GE</sub> = 0)	1300		V
I <sub>C</sub> <sup>(1)</sup>	Continuous collector current at T <sub>C</sub> = 25 °C	63	55	Α
I <sub>C</sub> <sup>(1)</sup>	Continuous collector current at T <sub>C</sub> = 100 °C 33 25		25	Α
I <sub>CL</sub> (2)	Turn-off latching current	40		Α
I <sub>CP</sub> <sup>(3)</sup>	Pulsed collector current	125		Α
V <sub>GE</sub>	Gate-emitter voltage	±25		V
P <sub>TOT</sub>	Total dissipation at T <sub>C</sub> = 25 °C	250	180	W
I <sub>F</sub>	Diode RMS forward current at T <sub>C</sub> = 25 °C	30		Α
I <sub>FSM</sub>	Surge non repetitive forward current $t_p = 10$ ms sinusoidal	100		Α
T <sub>j</sub>	Operating junction temperature	-55 to 1	150	°C

1. Calculated according to the iterative formula:

$$I_{C}(T_{C}) = \frac{T_{j(max)} - T_{C}}{R_{thj-c} \times V_{CE(sat)(max)}(T_{j(max)}, I_{C}(T_{C}))}$$

- 2.  $V_{clamp}$  = 960 V,  $T_j$  =150 °C,  $R_G$ =10  $\Omega$ ,  $V_{GE}$ =15 V
- 3. Pulse width limited by maximum permissible junction temperature and turn-off within RBSOA

Table 3. Thermal data

		Value		
Symbol Parameter		TO-3P, TO-247 long leads	TO-247	Unit
R <sub>thj-case</sub>	Thermal resistance junction-case IGBT	0.5	0.7	°C/W
R <sub>thj-case</sub>	Thermal resistance junction-case diode	2	2.1	°C/W
R <sub>thj-amb</sub>	Thermal resistance junction-ambient	50		°C/W

# 2 Electrical characteristics

 $T_J$ = 25 °C unless otherwise specified.

Table 4. Static

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
V <sub>(BR)CES</sub>	Collector-emitter breakdown voltage (V <sub>GE</sub> = 0)	I <sub>C</sub> = 1 mA	1300			V
V <sub>CE(sat)</sub>	Collector-emitter saturation voltage	V <sub>GE</sub> = 15 V, I <sub>C</sub> = 20 A V <sub>GE</sub> = 15 V, I <sub>C</sub> = 20 A, T <sub>J</sub> =125 °C		2.1 2.0	2.8	V V
V <sub>GE(th)</sub>	Gate threshold voltage	V <sub>CE</sub> = V <sub>GE</sub> , I <sub>C</sub> = 1 mA	3.75		5.75	V
I <sub>CES</sub>	Collector-cut-off current (V <sub>GE</sub> = 0)	V <sub>CE</sub> =1300 V V <sub>CE</sub> =1300 V, T <sub>J</sub> =125 °C			1 10	mA mA
I <sub>GES</sub>	Gate-emitter leakage current (V <sub>CE</sub> = 0)	V <sub>GE</sub> =± 20 V			± 100	nA
g <sub>fs</sub> <sup>(1)</sup>	Forward transconductance	V <sub>CE</sub> = 25 V <sub>,</sub> I <sub>C</sub> = 20 A		20		S
V <sub>F</sub>	Diode forward voltage	I <sub>F</sub> = 20 A I <sub>F</sub> = 20 A, T <sub>J</sub> = 125 °C		1.3	1.9 1.7	V V

<sup>1.</sup> Pulsed: pulse duration = 300 μs, duty cycle 1.5%

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
C <sub>ies</sub> C <sub>oes</sub> C <sub>res</sub>	Input capacitance Output capacitance Reverse transfer capacitance	V <sub>CE</sub> = 25 V, f = 1 MHz, V <sub>GE</sub> =0	-	2900 155 30	-	pF pF pF
$egin{array}{c} Q_{ m g} \ Q_{ m gc} \end{array}$	Total gate charge Gate-emitter charge Gate-collector charge	V <sub>CE</sub> = 960 V, I <sub>C</sub> = 20 A,V <sub>GE</sub> =15 V	-	127 18 50	-	n O O

Table 6. Inductive load switching times

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
$t_r(V_{off})$	Off voltage rise time	$V_{CC} = 960 \text{ V}, I_{C} = 20 \text{ A}$		102		ns
$t_{d(off)}$	Turn-off delay time	$R_{G}$ = 10 $\Omega$ , $V_{GE}$ = 15 $V$ ,	-	284	-	ns
t <sub>f</sub>	Current fall time	(see Figure 16)		180		ns
$t_r(V_{off})$	Off voltage rise time	$V_{CC} = 960 \text{ V}, I_{C} = 20 \text{ A}$		200		ns
$t_{d(off)}$	Turn-off delay time	$R_G$ = 10 $\Omega$ , $V_{GE}$ = 15 $V$ ,	-	424	-	ns
t <sub>f</sub>	Current fall time	T <sub>J</sub> = 125 °C (see Figure 16)		316		ns

Table 7. Switching energy (inductive load)

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
E <sub>off</sub> <sup>(1)</sup>	Turn-off switching losses	$V_{CC}$ = 960 V, $I_{C}$ = 20 A $R_{G}$ = 10 $\Omega$ , $V_{GE}$ = 15 V, (see Figure 16)	-	3.4	-	mJ
E <sub>off</sub> <sup>(1)</sup>	Turn-off switching losses	$V_{CC} = 960 \text{ V}, I_{C} = 20 \text{ A}$ $R_{G} = 10 \Omega, V_{GE} = 15 \text{ V},$ $T_{J} = 125 ^{\circ}\text{C} \text{ (see Figure 16)}$	-	6.4	-	mJ

<sup>1.</sup> Turn-off losses include also the tail of the collector current

## 2.1 Electrical characteristics (curves)

Figure 2. Output characteristics

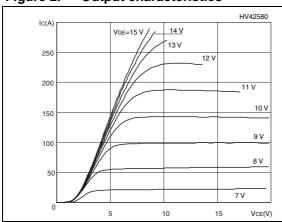


Figure 3. Transfer characteristics

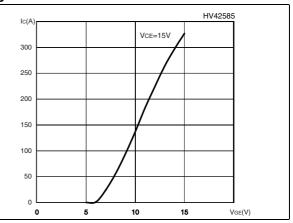
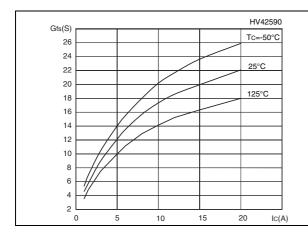


Figure 4. Transconductance

Figure 5. Collector-emitter on voltage vs. temperature



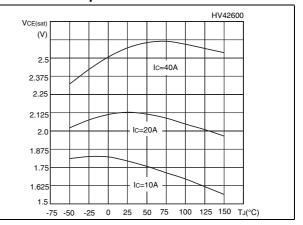
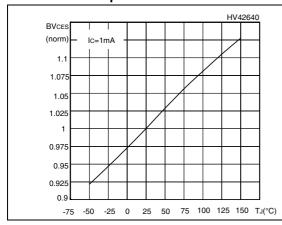


Figure 6. Normalized breakdown voltage vs. Figure 7. Gate-charge vs. gate-emitter temperature



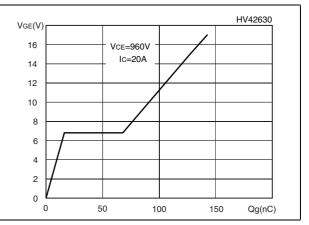


Figure 8. Normalized gate threshold voltage Figure 9. Collector-emitter on voltage vs. vs. temperature collector current

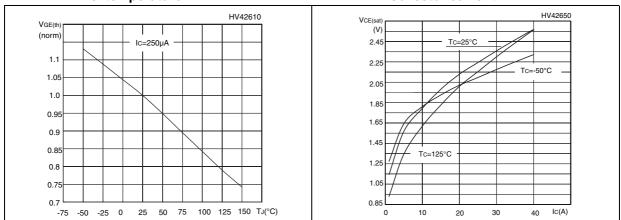


Figure 10. Switching losses vs. temperature

Figure 11. Switching losses vs. gate resistance

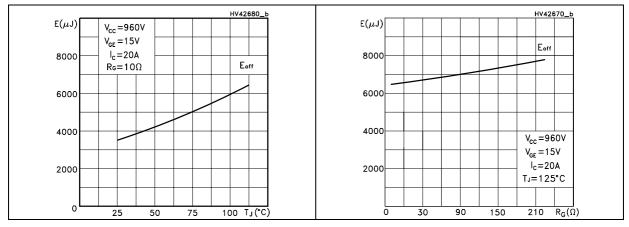


Figure 12. Switching losses vs. collector current

Figure 13. RBSOA

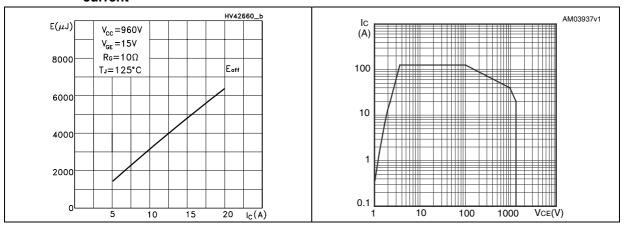
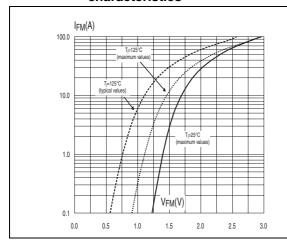
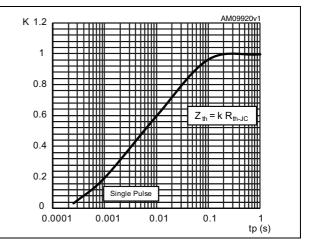


Figure 14. Emitter-collector diode characteristics

Figure 15. Thermal impedance





## 3 Test circuits

Figure 16. Test circuit for inductive load switching

Figure 17. Gate charge test circuit

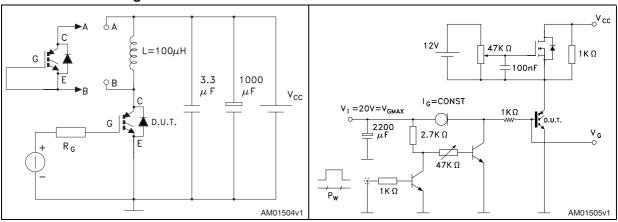
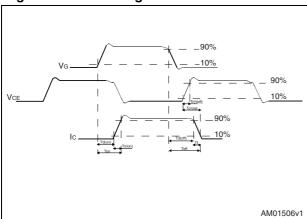


Figure 18. Switching waveform



# 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: *www.st.com*. ECOPACK<sup>®</sup> is an ST trademark.

Table 8. TO-247 mechanical data

Dim.		mm.	
Dilli.	Min.	Тур.	Max.
А	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
С	0.40		0.80
D	19.85		20.15
E	15.45		15.75
е	5.30	5.45	5.60
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
ØP	3.55		3.65
ØR	4.50		5.50
S	5.30	5.50	5.70

Figure 19. TO-247 drawing

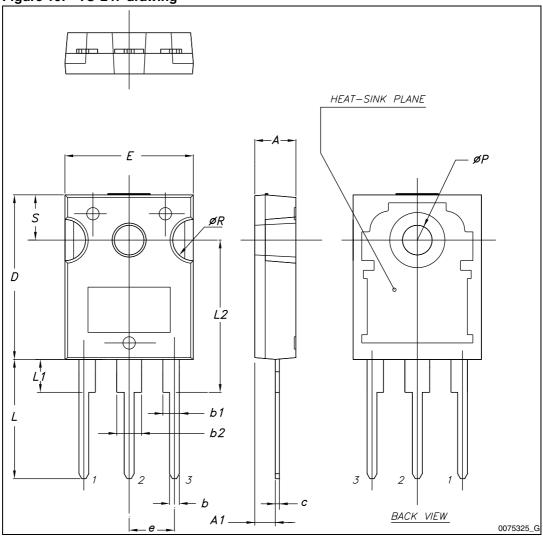


Table 9. TO-247 long leads mechanical data

Dim		mm	
Dim.	Min.	Тур.	Max.
Α	4.90		5.15
D	1.85		2.10
E	0.55		0.67
F	1.07		1.32
F1	1.90		2.38
F2	2.87		3.38
G		10.90 BSC	
Н	15.77		16.02
L	20.82		21.07
L1	4.16		4.47
L2	5.49		5.74
L3	20.05		20.30
L4	3.68		3.93
L5	6.04		6.29
М	2.27		2.52
V		10°	
V1		3°	
V3		20°	
Dia.	3.55		3.66

HEAT-SINK PLANE

LIST SINK PLANE

HEAT-SINK PLANE

BACK VIEW

7395426\_E

Figure 20. TO-247 long leads drawing

Table 10. TO-3P mechanical data

Package mechanical data

Dim		mm	
Dim.	Min.	Тур.	Max.
Α	4.60		5
A1	1.45	1.50	1.65
A2	1.20	1.40	1.60
b	0.80	1	1.20
b1	1.80		2.20
b2	2.80		3.20
С	0.55	0.60	0.75
D	19.70	19.90	20.10
D1		13.90	
E	15.40		15.80
E1		13.60	
E2		9.60	
е	5.15	5.45	5.75
L	19.50	20	20.50
L1		3.50	
L2	18.20	18.40	18.60
øΡ	3.10		3.30
Q		5	
Q1		3.80	

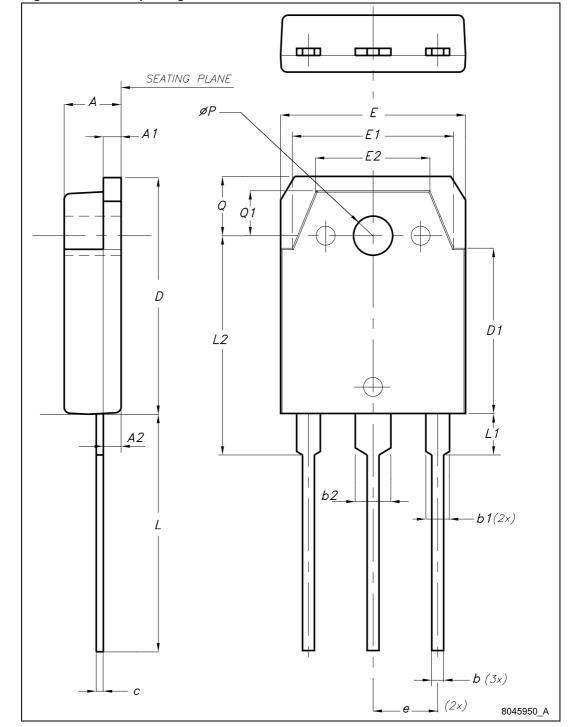


Figure 21. TO-3P package dimensions

# 5 Revision history

Table 11. Document revision history

Date	Revision	Changes
11-May-2009	1	Initial release
16-Jul-2009	2	Document status promoted from preliminary data to datasheet
05-Jul-2011	3	Added: Figure 15 on page 8 and new package mechanical data Table 10 on page 14, Figure 21 on page 15.
04-Sep-2012	4	Updated: Table 1 on page 1, TO-247 mechanical data Table 8 on page 10 and Figure 19 on page 11.

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